



《风光欣》技术资料

2SB624

PNP EPITAXIAL SILICON TRANSISTOR

*Features

High h_{FE} : 100~320

Low Collector Saturation Voltage

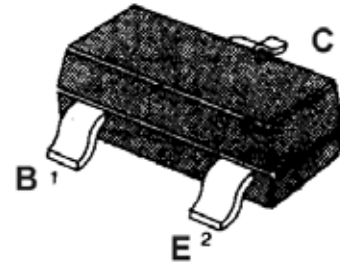
$V_{CE(sat)} = -0.5V(\text{Max.})$ $I_C = -500mA, I_B = -50mA$

Complementary Pair With 2SD596

ABSOLUTE MAXIMUM RATINGS($T_A = 25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-30	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter -Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-800	mA
Collector Dissipation	P_C	200	W
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-55 ~150	

SOT-23



ELECTRICAL CHARACTERISTICS ($T_A = 25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C = -500 \mu A, I_E = 0$	-30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1mA, I_B = 0$	-25			V
Emitter-Base Breakdown Voltage	BV_{EB0}	$I_E = -50 \mu A, I_C = 0$	-5			V
Collector Cut-off Current	I_{CB0}	$V_{CB} = -20V, I_E = 0$			-100	nA
Emitter Cut-off Current	I_{EB0}	$V_{EB} = -3V, I_C = 0$			-100	nA
DC Current Gain	h_{FE}	$V_{CE} = 1V, I_C = -50mA$	100		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-0.5	V
Transition Frequency	$f_T = 30MHz$	$V_{CE} = -5V, I_C = -10mA$		120		MHz
Collector Output Capacitance	$C_{ob} f=1MHz$	$V_{CB} = -10V, I_E = 0$		9		pF